

REMARKS

Claims 1, 6 and 16 have been amended to improve form and claims 5, 9-15 and 20 have been canceled without prejudice or disclaimer. Claims 1-4, 6-8 and 16-19 are now pending in this application.

Claims 1-8 and 16-20 have been rejected under 35 U.S.C. § 102(e) as being anticipated by Yu et al. (U.S. Patent No. 6,764,884; hereinafter Yu). The rejection is respectfully traversed.

Claim 1 recites a semiconductor device comprising a substrate, an insulating layer, a fin and silicided source and drain regions formed adjacent the fin. Claim 1, as amended, recites that the silicided source and drain regions are silicided down to the insulating layer. A similar feature was previously recited in original claim 5. As to original claim 5, the Office Action states that Yu discloses that the silicided source and drain regions are silicided down to the insulating layer and points to col. 8, lines 37-40 of Yu for support (Office Action – page 3). The applicants respectfully disagree.

Yu at col. 8, lines 37-40 corresponds to claim 6 which discloses depositing a metal over the source and drain regions 220/230 and annealing the semiconductor device to form a metal-silicide layer 520 over the source and drain regions (See Fig. 5B of Yu). This portion of Yu does not disclose that the silicided source and drain regions are silicided down to the insulating layer (i.e., buried oxide layer 120 in Fig. 5B), as required by amended claim 1.

For at least this reason, Yu does not disclose each of the features of amended claim 1. Accordingly, withdrawal of the rejection and allowance of claim 1 are respectfully requested. The applicants note that Yu is assigned to the same assignee as the present application. Therefore, Yu is not available as prior art under 35 U.S.C. § 103 in accordance with 35 U.S.C. § 103(c).

Claims 2-4 and 6-8 are dependent on claim 1 and are believed to be allowable over Yu for at least the reasons claim 1 is allowable. Accordingly, withdrawal of the rejection and allowance of claims 2-4 and 6-8 are respectfully requested.

Claim 16, as amended, recites silicided source and drain regions having a thickness ranging from about 400 Å to about 1500 Å formed on the opposite sides of the metal gate. A similar feature was previously recited in original claim 20. As to original claim 20, the Office Action states that Yu discloses that the thickness of the silicided source and drain regions ranges from about 400 Å to about 1500 Å and points to col. 4, lines 30-34 for support (Office Action – page 4). The applicants respectfully disagree.

Yu at col. 4, lines 30-34 discloses that dummy gate 300 may have a thickness ranging from about 300 Å to about 1000 Å and a width ranging from about 50 Å to about 500 Å. This portion of Yu does not disclose that the thickness of the silicided source and drain regions (e.g., regions 220 and 230 in Fig. 5B) ranges from 400 Å to about 1500 Å, as required by amended claim 16. In contrast, Yu discloses that metal layer 510 used to form metal-silicide layer 520 is deposited to a thickness ranging from about 50 Å to about 200 Å (Yu – col. 4, lines 49-58).

For at least this reason, Yu does not disclose each of the features of claim 16. Accordingly, withdrawal of the rejection and allowance of claim 16 are respectfully requested.

Claims 17-19 are dependent on claim 16 and are believed to be allowable over Yu for at least the reasons claim 16 is allowable. Accordingly, withdrawal of the rejection and allowance of claims 17-19 are respectfully requested.

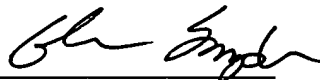
CONCLUSION

In view of the foregoing amendments and remarks, the applicants respectfully request withdrawal of the outstanding rejection and the timely allowance of this application.

To the extent necessary, a petition for an extension of time under 37 C.F.R. § 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 50-1070 and please credit any excess fees to such deposit account.

Respectfully submitted,

HARRITY & SNYDER, L.L.P.

By: 
Glenn Snyder
Reg. No. 41,428

Date: January 4, 2005
11240 Waples Mill Road
Suite 300
Fairfax, VA 22030
Telephone: (571) 432-0800
Facsimile: (571) 432-0808